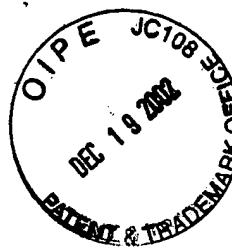


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicants: Halahan, Patrick B.; Siniaguine, Oleg
 Assignee: Tru-Si Technologies, Inc.
 Title: Semiconductor Structures Having Multiple Conductive Layers In An Opening, And Methods For Fabricating Same
 Application No.: 09/941,447 Filing Date: 08/28/2001
 Examiner: Thomas, Toniae M. Group Art Unit: 2822
 Docket No.: M-9999-1D US

San Jose, California
 19 December 2002

COMMISSIONER FOR PATENTS
 Washington, D.C. 20231

RESPONSE TO RESTRICTION REQUIREMENT

Sir:

Responsive to the Restriction Requirement mailed 19 November 2002, Applicants' attorney provisionally elects Species I directed to removing material along the second side of the substrate so that the first and second conductive layers protrude out of the opening with the second conductive layer protruding further than the first conductive layer.

Dependent Claims 35, 44, 59, and 74 specifically read on elected Species I.

Claim 34 depends from independent Claim 1 by way of dependent Claims 33 and 34. Claim 44 depends from Claim 1 by way of dependent Claims 2, 42, and 43. Claim 59 depends from Claim 1 by way of dependent Claims 4, 54, 55, 57, and 58. Claim 74 depends from independent Claim 20 by way of dependent Claims 68 and 71 - 73. Accordingly, Claim 1, 2, 4, 20, 33, 34, 42, 43, 54, 55, 57, 58, 68, and 71 - 73 are also deemed readable on elected Species I. Hence, the claims readable on Species I consist at least of Claims 1, 2, 4, 20, 33 - 35, 42 - 44, 54, 55, 57 - 59, 68, and 71 - 74.

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